

**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

**IN THE SPECIFICATION:**

Please amend the specification as follows:

Page 21, please replace paragraph [0080] with the following replacement paragraph:

--Referring to Fig. 2, a motherboard 9 is manufactured considering organic material, such as glass epoxy, as a base. The motherboard 9 is provided at the inner layer and outer layer with copper wiring patterns. The motherboard 9 is also provided at both upper and lower surfaces with terminals on which semiconductor [chips] devices and chips are mounted. A semiconductor device 8 and chips, such as resistances and capacitors, are mounted on the motherboard 9 using solder paste.--

Page 22, please replace paragraph [0084] with the following replacement paragraph:

--The semiconductor chip 103 is mounted on the die pad 101 using conductive paste 102. In the drawings, "P" represents a power supply terminal and "G" represents a ground terminal. The inner leads 105, connected to the power supply terminals P and ground terminals G<sub>1</sub> are extended inwardly toward the semiconductor chip 103. A chip capacitor mounting pad 111 is formed at the inner ends of the adjacent two extended inner leads 105. A chip capacitor 110 is mounted on each of the chip capacitor mounting pads 111 using conductive adhesives 112, such as silver-epoxy system

adhesives or solder paste. All of the semiconductor chip 103, chip capacitors 110 and inner leads 105 are molded with the mold resin 106 entirely.--

Page 64, please replace paragraph [0202] with the following replacement paragraph:

--According to this embodiment, a copper layer is formed on a surface of an organic material substrate 1821, and the copper layer is etched to form a conductive pattern (wiring pattern) 1822. The wiring [patter] pattern 1822 (1822p, 1822g) is connected via through holes 1823 to ball mounting pads 1824, formed on the opposite surface of the organic material substrate 1821. A solder resist 1826 is selectively formed on the both surface of the organic material substrate 1821.--

Page 68, please replace paragraph [0211] with the following replacement paragraph:

--According to this embodiment, a copper layer is formed on a surface of an organic material substrate 1921, and the copper layer is etched to form a conductive pattern (wiring pattern) 1922. The wiring [patter] pattern 1922 ([1822p, 1822g] 1922p, 1922g) is connected via through holes 1923 to ball mounting pads 1924, formed on the opposite surface of the organic material substrate 1921. A solder resist 1926 is selectively formed on the both surface of the organic material substrate 1921.--

**IN THE CLAIMS:**

Please cancel claims 1-45 without prejudice or disclaimer to the subject matter recited therein.

Please amend the claims as follows:

46. (Amended) A semiconductor apparatus<sub>1</sub> comprising:

[an organic material] a substrate;

a die pad which comprises a power supply bonding area which is formed by extending outwardly all the sides of the die pad;

ground terminals which are to be grounded;

power supply terminals which are supplied with electrical power;

first conductive patterns which are formed on the [organic material] substrate and are connected to the ground terminals;

second conductive patterns which are formed on the [organic material] substrate and are connected to the power supply terminals and the power supply bonding area;

a high dielectric constant layer formed on the die pad; and

a metal layer formed [between] on the high dielectric constant layer and [die pad to have] having a chip mounting area on which a semiconductor chip is [mounted] mountable and a ground bonding area surrounding the chip mounting area, the ground bonding area being connected to the first conductive patterns.

47. (Amended) A semiconductor apparatus according to claim 46, wherein the metal layer is provided with a [projection or] ridge surrounding the chip mounting area so as to define the chip mounting area and ground bonding area.

48. (Amended) A semiconductor apparatus according to claim 46, wherein the high dielectric constant layer is composed of ceramics[, such as alumina (aluminum oxide) and titan oxide].